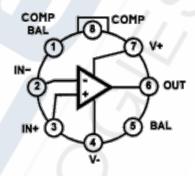


#### **Features**

- Offset voltage 3 mV maximum over temperature
- Input current 100 nA maximum over temperature
- Offset current 20 nA maximum over temperature
- Guaranteed drift characteristics
- Offsets guaranteed over entire common mode and supply voltage ranges
- Slew rate of 10V/us as a summing amplifier

#### **Pinout**

8-lead metal can Top View



Package pinout

### **Operational Amplfiers**

The FT101ASH5U is a general purpose operational amplifier which features improved performance over industry standards such as the LM709. Advanced processing techniques make possible an order of magnitude reduction in input currents, and a redesign of the biasing circuitry reduces the temperature drift of input current. This amplifier offers many features which make its application nearly foolproof: overload protection on the input and output, no latch up when the common mode range is exceeded, and freedom from oscillations and compensation with a single 30pF capacitor. It has advantages over internally compensated amplifiers in that the frequency compensation can be tailored to the particular application. For example, in low frequency circuits it can be overcompensated for increased stability margin. Or the compensation can be optimised to give more than a factor of ten improvement in high frequency performance for most applications. In addition, the device provides better accuracy and lower noise in high impedance circuitry. The low input currents also make it particularly well suited for long interval integrators or timers, sample and hold circuits and low frequency waveform generators. Further, replacing circuits where matched transistor pairs buffer the inputs of conventional IC op amps, it can give lower offset voltage and a drift at a lower cost.



## **Absolute Maximum Ratings**

Supply Voltage ±22V
Differential Input Voltage ±30V
Input Voltage(Note 2) ±15V
Output Short Circuit Duration(Note 3) Continuous
Total Power 750mW
Storage Temperature Range -65°C <Ta<+150°C
ESD Tolerance(Note 4) 3500V
Notes:

- 2. The maximum power dissipation must be derated at elevated temperatures and is dictated by Tjmax (maximum junction temperature), ThetaJA (package junction to ambient thermal resistance), and TA (ambient temperature). The maximum allowable power dissipation at any temperature is Pdmax = (Tjmax TA)/ThetaJA or the number given in the Absolute Maximum Ratings, whichever is lower.
- 3. For supply voltages less than +15V, the absolute maximum input voltage is equal to the supply voltage.
- 4. Human body model, 100 pF discharged through 1.5k Ohms.

#### **Thermal Information**

Thermal Resistance (typical)  $\theta_{JA} = 170 \text{ °C/W (note 1)}$ 

 $\theta_{JC} = 85 \text{ °C/W (note 2)}$ 

**Maximum Junction Temperature** 

150°C

300°C

Lead Temperature

(Soldering, 10 seconds)

Notes:

- 5.  $\theta_{JA}$  is measured with component on an evaluation PC board in free air
- 6. For  $\theta_{\text{JC}}$  "case temp" location is the center of metal can

## **Electrical Specifications**

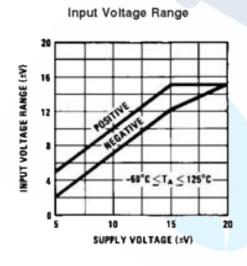
 $V_{SUPPLY} = \pm 15 \text{ V}$ 

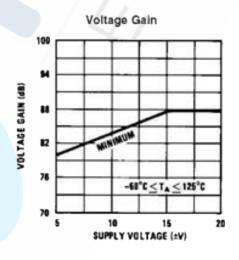
Parameter	Temp., °C	FT101ASH5U/ FT201ASH5A			FT301ASH5J			Units
		Min	Тур	Max	Min	Тур	Max	
		Input (	Characteris	tics				
Input Offset Voltage ,	25	-2	0.5	2	-2	0.5	2	
•	Tmax	-3	-	3	-3	-	3	mV
Rs ≤ 50kΩ	Tmin	-3	-	3	-3	-	3	
Offset Voltage Drift , Rs ≤ 50kΩ		-15	10	15	-15	10	15	μV/°C
	25	-	30	75	-	30	75	
Input Bias Current	Tmax	1	15	75	-	20	75	nA
	Tmin	-	45	100	-	35	100	
Input Offset Current	25	-10	-	10	-10	-	10	
Imput Offset Current	Tmax	-10	-	10	-10	-	10	nA
	Tmin	-20	-	20	-20	-	20	
Offset Current Drift	25 to Tmax	-0.1	0.05	0.1	-0.1	0.05	0.1	nA/°C
Onset Current Dilit	Tmin to 25	-0.2	0.07	0.2	-0.2	0.07	0.2	TIA, C

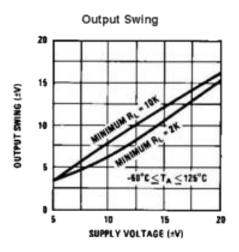


Parameter	Temp., °C		Г101ASH5 Г201ASH5	-	FT301ASH5J			Units
	L	Min	Тур	Max	Min	Тур	Max	
Maximum Common Mode	25	+11	+13	-	+11	+13	/ -(	
Voltage, $R_L$ = 2k $\Omega$	Tmax	+11	+13	-	+11	+13	1	V
Voltage,N[-2K12	Tmin	+11	+13	1	+11	+13	/-/	A
Minimum Common Modo	25	-	-13	-11	1	-13	-11	
Minimum Common Mode Voltage	Tmax	-	-13	-11	-	-13	-11	V
	Tmin	-	-13	-11		-13	-11	
Input Resistance	25	1.5	4	-	1.5	4	-	kΩ
		Transfer c	haracteris	tics				
Largo Signal Voltago Gain	25	80	160	-	80	160	-	
Large Signal Voltage Gain V <sub>OUT</sub> =±10V,R <sub>L</sub> =2kΩ	Tmax	80	160	-	80	160	1	kV/V
V <sub>0UT</sub> -±10V,N <sub>L</sub> -2K\$2	Tmin	40	80	-	40	80	1	
Common Mada Rajastian	25	80	96	-	80	96	1	
Common Mode Rejection Ratio , Rs ≤ 50kΩ	Tmax	80	85	-	80	85	1	dB
Natio, NS \( \) SUK\$2	Tmin	80	85	-/	80	85	1	
Power Supply Characteristics				//				
	25	-	1.5	2.0	-)	1.5	2.0	
Supply Current	Tmax	-	1.2	2.0		1.2	2.0	mA
	Tmin	-	2.0	3.0		2.0	3.0	
Supply Voltage Rejection Ratio, Rs ≤ 50kΩ	25	80	96	<u></u>	70	96	-	dB

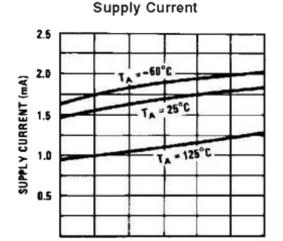
# **Typical Performance Characteristics**











### Maximum Power Dissipation

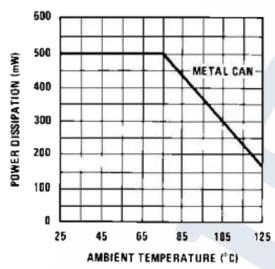
SUPPLY VOLTAGE (±V)

10

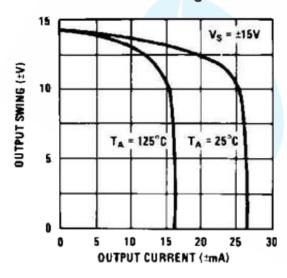
5

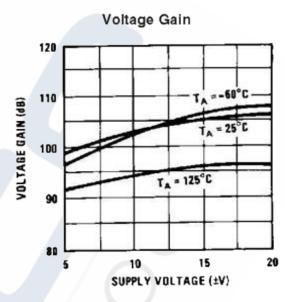
20

15

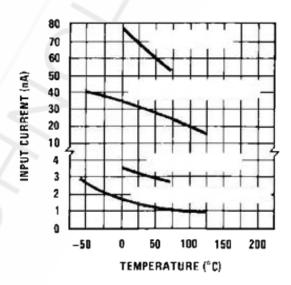


**Current Limiting** 

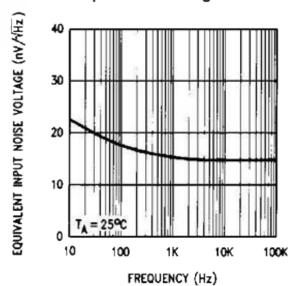




Input Current,



Input Noise Voltage





#### **Die Characteristics**

Die dimensions:

1.3x1.2± 0.1 mm,

51x47 ± 4 mils.

Wafer thickness 0.46± 0.02 mm,

18 ± 1 mils.

Metallisation:

type: Al, 1% Si, thickness:  $1.4 \pm 0.1 \mu m$ 

Glassivation:

type: Phosphosilicate glass (PSG) PSG thickness 1.2 ±0.2μm. Worst case current density:

 $8.10^4 \text{ A/cm}^2$ .

Substrate potential(Powered Up):

Unbiased.

Transistor count:

24.

Process:

Bipolar epitaxial.

9AII

BAL

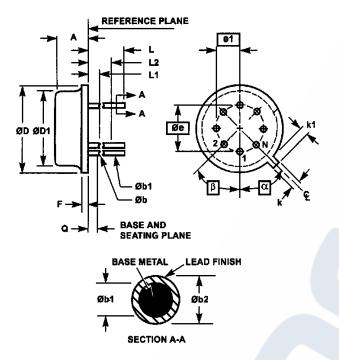
## **Metallisation Mask layout**

# BAL, COMP -IN +IN

COMP



## Metal Can Package



#### Notes:

- (All leads) Øb applies between L1 and L2. Øb1 applies between L2 and 0.500 from the reference plane. Diameter is uncontrolled in L1 and beyond 0.500 from the reference plane.
- Measured from maximum diameter of the product.
- $\alpha$  is the basic spacing from the centerline of the tab to terminal 1 and  $\beta$  is the basic spacing of each lead or lead position (N -1 places) from a, looking at the bottom of the package.
- N is the maximum number of terminal positions.
- Controlling dimension: millimeter.

SH-8 8-lead metal can package

	Millin	neters	Inc			
Symbol	MIN	MAX	MIN	MAX	Note	
Α	6.00	6.22	0.236	0.244	_	
Øb	0.41	0.48	0.016	0.019	13	
Øb1	0.41	0.53	0.016	0.021	13	
Øb2	0.41	0.61	0.016	0.024	-	
ØD	9.09	9.19	0.335	0.375	-	
ØD1	8.23	8.43	0.305	0.335	-	
Øe	0.2	.00	5.	-		
e1	0.1	.00	2.	-		
F	0.33	0.43	0.013	0.017	_	
k	0.69	0.86	0.027	0.034	-	
k1	0.69	1.14	0.027	0.045	14	
L	13.0	14.0	0.512	0.552	13	
L1	_	1.27	-	0.05	13	
L2	6.35	6.85	0.250	0.270	13	
Q	0.5	)_	0.02	-	-	
α	4!	5°	4.	15		
β	45°		4.	15		
N	8	3	8	16		

#### **Ordering Information**

Part	Mark.	Temp., °C	Package	Package Drawing
FT101ASH5U	101A5U	-60 to +125	8-lead	
FT201ASH5J	201A5A	-40 to +85	metal can	SH-8
FT301ASH5U	301A5J	0 to +70		

Notes :1. These Pb-free hermetic packaged products employ 100% Au plate, which is RoHS.



# **Revision History**

Ũ⁄Ác	ΔΩæΛ	Description
<u> </u>	<b>. Dæc</b> ? 20/405/13	Original
	20/03/13	Original
	1	
	1	



Á Rev. 1

<sup>A</sup> Á Мау 2013



Ashley Crt, Henley, Marlborough, Wilts, SN8 3RH UK

Tel: +44(0)1264 731200 Fax:+44(0)1264 731444

E-mail: sales@forcetechnologies.co.uk

www.forcetechnologies.co.uk

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